	PRODUCTS	TYF	TYPE PAG		
ROHM	Semiconduc	tor IC	BH1426KN		1/4
TRUCTURE RODUCT SERIES YPE EATURE	BH1426KN Low voltage Fa Adjustment free Possible to sele Possible to sele Possible to sele Built-in high per 	nk LSI for Mobile st Mode I ² C-BUS wideband PLL f ect reference cloc ect transmission ect pre-emphasis formance Low-p	Phone (FM Stereo T interface. requency synthesized k frequency freely. power by serial contro time constant by ser	r (76MHz~108MHz). bl. ial control.	
) Absolute Maximum Rat	 The transmission Possible to ope Built-in the source 	on frequency is s rate in monaural	able because it has i mode.	PLL system FM transm	litter circu
Parameter	Symbol	Limits	Unit	Condition	
Supply voltage	VCC	-0.3 to +	5.5 V	V Pin 2, 7, 11, 13, 25	
Data input voltage 1	V _{IN-D1}	-0.3 to VDDI	0+0.3 V	V Pin 16, 19, 20	
Data input voltage 2	V _{IN-D2}	-0.3 to VCC V Pin 17, 18		Pin 17, 18	
Power dissipation	Pd	370	mW	(Alata 1)	
Power dissipation		0/0	1	(Note 1)	
Storage temperature	Tstg emperature higher that	-55 to +1	25 °C		
Storage temperature (Note 1) To use at a to (Note 1) To use at a to tatus of this document he Japanese version of this docu ersion. If there are any differences solication example OHM cannot provide adequate he product described in this so ffice-automation equipment, co	emperature higher that ment is the formal specificatio s in translation version of this confirmation of patents. pecification is designed to ommunications devices, ele	-55 to +1 <i>n Ta=25 °C, derati</i> <i>n.</i> A customer may us document, formal vers be used with ordina ctrical appliances, a	25 °C e 3.7mW per 1 °C. e this translation version on ion takes priority. ry electronic equipment on electronic toys).	ly for a reference to help read	visual equip
Storage temperature (Note 1) To use at a tage (Note 1) To use at a tage atus of this document he Japanese version of this docu ersion. If there are any differences lication example OHM cannot provide adequate he product described in this s	emperature higher that ment is the formal specificatio s in translation version of this confirmation of patents. pecification is designed to product with equipment or life (such as medical instru- ices), please be sure to con lity for use of any circuits are free from patent infring APPROVAL	-55 to +1 <i>n Ta=25 °C, derate</i> <i>n.</i> A customer may us document, formal verses be used with ordina ctrical appliances, a devices which requi uments, transportati sult with our sales r described herein, o	25 °C e 3.7mW per 1 °C. e this translation version on ion takes priority. ry electronic equipment on delectronic toys). re an extremely high leve on equipment, aerospace epresentative in advance. conveys no license under	ly for a reference to help read or devices (such as audio-v el of reliability and the malf machinery, nuclear-reacto	visual equip function of r controller t, and mak

$\bigcirc\,$ Operating Supply Voltage Range

Parameter	Symbol	Limits	Unit	Conditions
Operating supply voltage 1	Vcc	2.7 to 3.6	V	Pin 2, 7, 11, 25
Operating supply voltage 2	V _{DDIO}	1.7 to 3.6	V	Pin 13
Operating temperature	Tpor	-20 to +85	°C	
Audio input level	V _{IN-A}	to -10	dBV	Pin 26, 27
Audio input frequency	f _{IN-A}	20 to 15k	Hz	Pin 26, 27
Transmission frequency	f _{TX}	76.0 to 108.0	MHz	100kHz step
Control terminal "H" level input voltage 1	V _{IH1}	0.7VDDIO to VDDIO	V	Pin 16, 19, 20
Control terminal "H" level input voltage 2	V _{IH2}	0.7V _{DDIO} to +5.5	v	Pin 17, 18
Control terminal "L" level input voltage	VIL	GND to 0.3VDDIO	v	Pin 16, 17, 18, 19, 20

TYPE

○ Electrical Characteristics

Unless otherwise specified Ta=25°C, V_{CC} =3.0V, V_{DDIO} =1.8V

Signal source : f _{IN} =1kHz, V _{IN} =-20dBV	Common condition : $f_{TX}=90MHz$, $\Delta f=\pm75kHz$, $\tau=50 \mu s$

Parameter	Symbol	Limits			Unit	Condition	
		Min.	Тур.	Max.	Unit	Condition	
Quiescent current	۱a	11	16	23	mA	Tx Control : 0dB	
Power down current	I _{PWD}	_	0	1	μA	BUSEN = "L"	
Channel separation	Sep	25	40	_	dB	L→R, R→L	
Signal to noise ratio	SNR	60	69	-	dB	L+R	
		61	70	—	dB	ΜΟΝΟ	
Total harmonic distortion	THD	_	0.1	0.3	%	L+R	
			0.1	0.3	%	MONO	
Transmission power level	Ρτχ	-8	-5	-2	dBm	Tx Control : 0dB	
Pilot modulation rate	MP	7	11	15	%	L+R	
"H" level input current	Iн	-	-	1.0	μA	Pin 16, 19, 20 V _{IN} =3V	
"L" level input current	l _{iL}	-1.0	-	-	μA	Pin 16, 19, 20 V _{IN} =0V	
"L" level output voltage	V _{OL}	_	_	0.2V _{DDIO}	V	Pin 18 I ₀ =3mA	

◎ This product is not designed for protection against radioactive rays.

REV. :

◎ The specification of transmission output level be based on the Radio Law in every country and the area.

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- O Cautions on use
- (1) Numbers and data in entries are representative design values and are not guaranteed values of the items.
- (2) Although we are confident in recommending the sample application circuits, carefully check their characteristics further when using them. When modifying externally attached component constants before use, determine them so that they have sufficient margins by taking into account variations in externally attached components and the Rohm LSI, not only for static characteristics but also including transient characteristics.

TYPE

(3) Absolute maximum ratings

If applied voltage, operating temperature range, or other absolute maximum ratings are exceeded, the LSI may be damaged. Do not apply voltages or temperatures that exceed the absolute maximum ratings. If you think of a case in which absolute maximum ratings are exceeded, enforce fuses or other physical safety measures and investigate how not to apply the conditions under which absolute maximum ratings are exceeded to the LSI.

(4) GND potential

Make the GND pin voltage such that it is the lowest voltage even when operating below it. Actually confirm that the voltage of each pin does not become a lower voltage than the GND pin, including transient phenomena.

(5) Thermal design

Perform thermal design in which there are adequate margins by taking into account the allowable power dissipation in actual states of use.

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